



PT9702B

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI PT9702B** is a Common Emitter Device Designed for Class AB and C Amplifier Applications in the 220 - 400 MHz Military Communications Band.

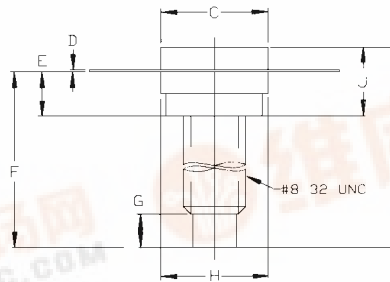
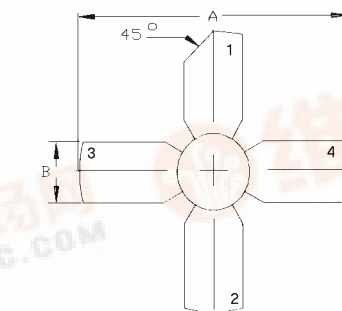
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- High Gain

MAXIMUM RATINGS

I_C	2.0 A
V_{CES}	60 V
V_{CEO}	30 V
P_{DISS}	40 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-55°C to $+200^\circ\text{C}$
θ_{JC}	4.0°C/W

PACKAGE STYLE .280 4L STUD



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25.65	1.055/26.80
B	.220/5.59	.230/5.84
C	.270/6.86	.285/7.24
D	.003/0.08	.007/0.18
E	.117/2.97	.137/3.48
F	.5/12.7	.53/13.5
G	.130/3.30	.137/3.48
H	.275/6.99	.285/7.24
I	.640/16.26	.648/16.46
J	.175/4.45	.21/5.31

1 = COLLECTOR 2 = BASE
3 & 4 = EMITTER

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 20\text{ mA}$	30			V
BV_{CES}	$I_C = 20\text{ mA}$	60			V
BV_{EBO}	$I_E = 2.0\text{ mA}$	4.0			V
I_{CBO}	$V_{CB} = 30\text{ V}$			2.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	10		150	---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			24	pF
P_G η_c	$V_{CE} = 28\text{ V}$ $P_{out} = 20\text{ W}$ $f = 400\text{ MHz}$	7.0 60			dB %